

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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10/798,475

Filing Date:

March 10, 2004

Confirmation No.:

Unassigned

First Named Inventor:

Yi Ding

Assignee:

ProMOS Technologies, Inc.

Examiner:

Unassigned

Art Unit:

Unassigned

Attorney Docket No.:

M-15296 US

San Jose, California April 16, 2004

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

## INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(b)

Dear Sir:

Pursuant to 37 CFR § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying form PTO-1449 are called to the attention of the Examiner for the above patent application. Copies of these documents are enclosed except for United States Patents and United States Published Patent Applications.

Citation of these documents shall not be construed as:

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- 3. an admission that the information cited herein is, or is considered to be material to patentability as defined in § 1.56(b).

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I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on April 16, 2004.

Attorney for Applicant(s)

Date of Signature

Respectfully submitted,

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Michael Sherker

U.S. Department of Commerce, Patent and Trademark Office				Atty Docket No.			Serial No.		
				M-15297 US			10/797,972		
FERMATION DISCLOSURE STATEMENT BY APPLICANT				Applicant(s)					
(Use several sheets if necessary)				Yi Ding					
APR 2 0 2004 (2)				Filing Date			Group		
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<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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